AUTOMOTIVE

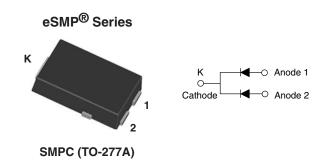
COMPLIANT

HALOGEN FREE



Vishay Semiconductors

Hyperfast Rectifier, 2 x 4 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _{F(AV)}	2 x 4 A			
V_R	200 V			
V _F at I _F	0.72 V			
t _{rr (typ.)}	25 ns			
T _J max.	175 °C			
Package	SMPC (TO-277A)			
Circuit configuration	Common cathode			

FEATURES

- \bullet Hyperfast recovery time, reduced $\mathbf{Q}_{\mathrm{rr}},$ and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- · Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 gualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMPC (TO-277A)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per

J-STD-002

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V _{RRM}		200	V
Average rectified forward current per dev	per device	I _{F(AV)}	T _{Sp} = 160 °C	8	А
Average rectilied forward current	per diode			4	
Non-repetitive peak surge current per device per diode	per device	I _{FSM}	T _J = 25 °C	130	
	per diode			70	
Operating junction and storage temperatures		T _J , T _{Stg}		-55 to +175	°C



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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-	
Forward voltage, per diode V _F	W	I _F = 4 A	-	0.89	0.95	V
	V _F	I _F = 4 A, T _J = 150 °C	-	0.72	0.78	
Reverse leakage current, per diode		V _R = V _R rated	-	-	2	
	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	6	80	μΑ
Junction capacitance	C _T	V _R = 200 V	-	17	-	pF

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST (TEST CONDITIONS		TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A, } dI_F/c$	$dt = 50 \text{ A/}\mu\text{s}, V_{R} = 30 \text{ V}$	1	25	-	
Reverse recovery time		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	25	l no
	t _{rr}	T _J = 25 °C	I _F = 4 A dI _F /dt = 200 A/μs V _R = 160 V	-	18	-	ns
		T _J = 125 °C		-	27	-	
Peak recovery current	I	T _J = 25 °C		-	2	-	A
Peak recovery current I _{RRM}	IRRM	T _J = 125 °C		-	3.6	-	
Povorno ropovoni oborgo	Reverse recovery charge Q _{rr}	T _J = 25 °C		-	18	-	nC
neverse recovery charge		T _J = 125 °C		-	50	-	110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to mount, per leg	R_{thJM}		-	2.5	3.5	°C/W
Thermal resistance, junction to ambient, per leg	R _{thJA}		-	80	-	°C/W
Approximate weight				0.1	•	g
Approximate weight				0.0035	•	oz.
Marking device		Case style SMPC (TO-277A)		QC	H2	•

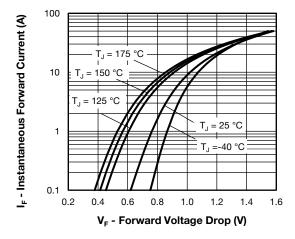


Fig. 1 - Typical Forward Voltage Drop Characteristics

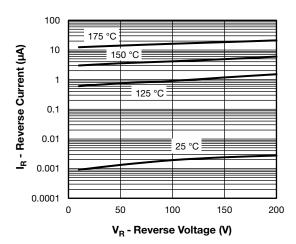


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

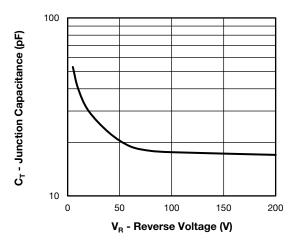


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

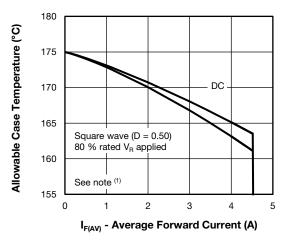


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

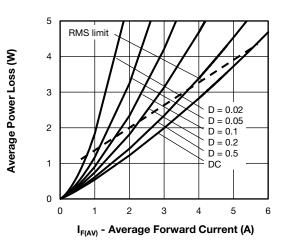


Fig. 5 - Forward Power Loss Characteristics

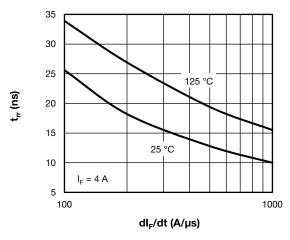


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

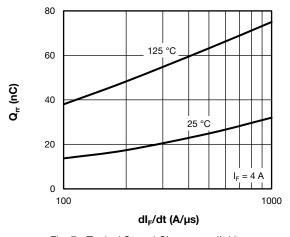


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

 $[\]begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$

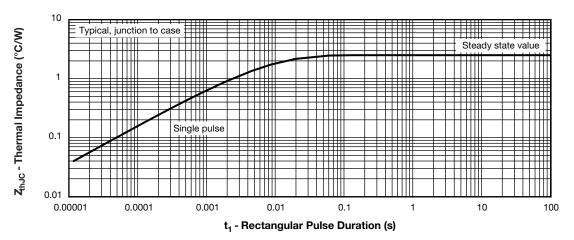


Fig. 8 - Typical Transient Thermal Impedance, Junction to Case

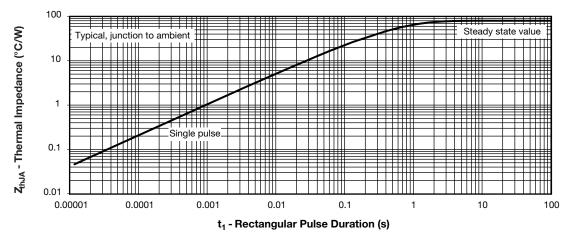
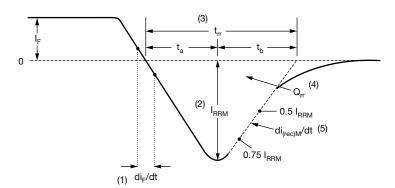


Fig. 9 - Typical Transient Thermal Impedance, Junction to Ambient



- di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RBM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

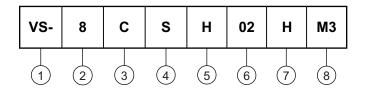
Fig. 10 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (8 = 8 A)

- Circuit configuration:

C = common cathode

4 - S = SMPC package

Process type,

H = hyper fast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

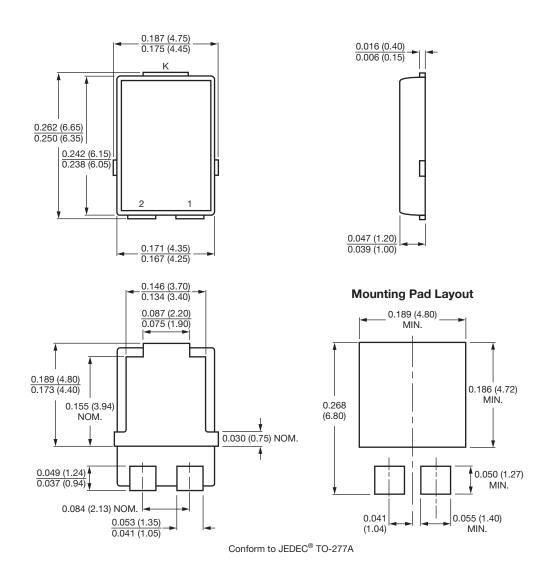
ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-8CSH02HM3/86A	1500	1500	7" diameter plastic tape and reel		
VS-8CSH02HM3/87A	6500	6500	13" diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95570</u>				
Part marking information	www.vishay.com/doc?95565			
Packaging information	www.vishay.com/doc?88869			
SPICE model	www.vishay.com/doc?96095			

Vishay Semiconductors

TO-277A (SMPC)

DIMENSIONS in inches (millimeters)





Vishay

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